

1SS413

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

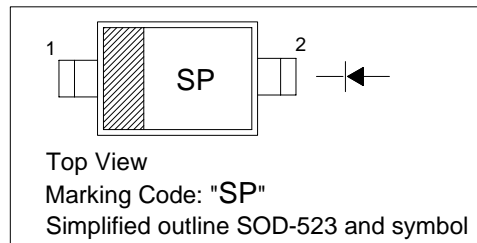
High Speed Switching Application

Features

- Low forward voltage : $V_{F(3)}=0.50V(\text{typ.})$.
- Low reverse current : $I_R=0.5\mu A(\text{max.})$.
- Small total capacitance : $C_T=3.9pF(\text{typ.})$.

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



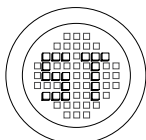
Absolute Maximum Ratings ($T_j = 25^\circ C$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V_R	20	V
Peak Forward Current	I_{FM}	100	mA
Average Forward Current	I_O	50	mA
Surge Current (10ms)	I_{FSM}	1	A
Power Dissipation (Note 1)	P_{tot}	100	mW
Junction Temperature	T_J	125	?
Storage Temperature	T_s	-55 to +125	?

Note 1: Mounted on a glass epoxy circuit board of 20x20 mm, pad dimension of 4x4 mm.

Characteristics at $T_j = 25^\circ C$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	$I_F = 1mA$	$V_{F(1)}$	-	0.33	-	V
	$I_F = 5mA$	$V_{F(2)}$	-	0.38	-	V
	$I_F = 50mA$	$V_{F(3)}$	-	0.50	0.55	V
Reverse Current	$V_R = 20V$	I_R	-	-	0.5	μA
Total Capacitance	$V_R = 0V, f = 1MHz$	C_T	-	3.9	-	pF



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РАДИОТЕХ-ТРЕЙД

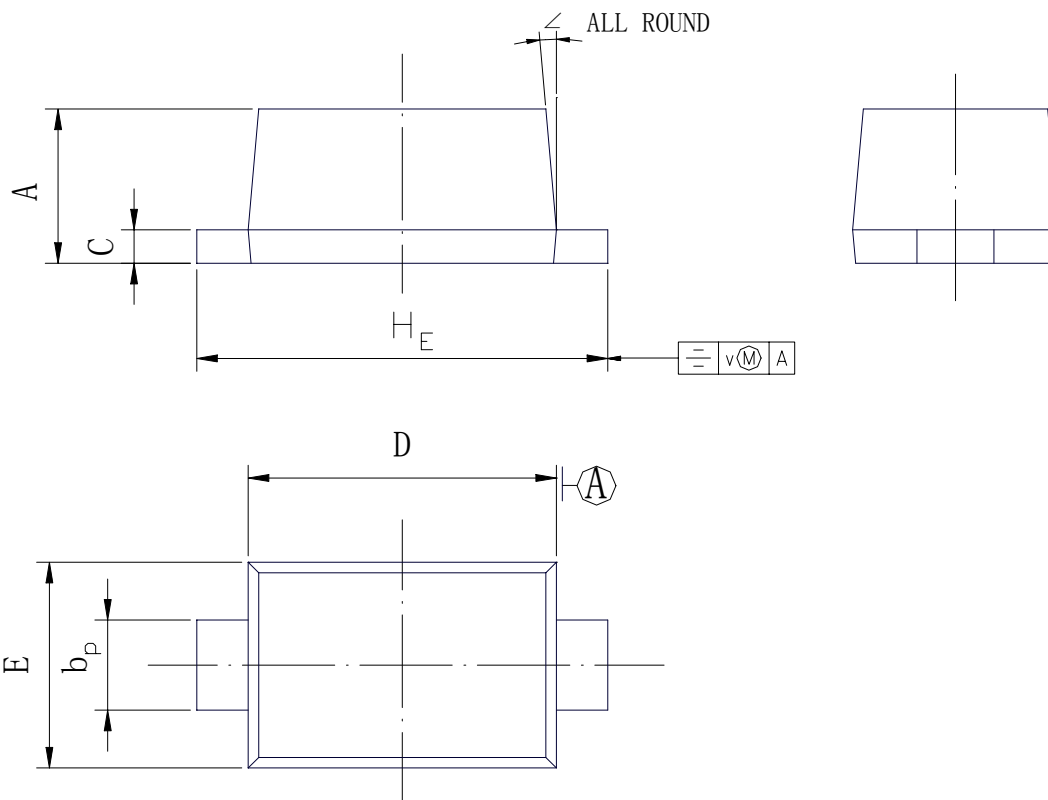
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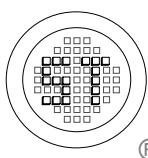
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	v	∠
mm	0.70 0.60	0.4 0.3	0.135 0.127	1.25 1.15	0.85 0.75	1.65 1.55	0.1	5°



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



ISO 9001 : 2000
Certificate No. 020-100-0102-001

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